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# Ion Beams in Materials Processing and Analysis

 Springer

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ISBN 978-3-211-99355-2                      ISBN 978-3-211-99356-9 (eBook)  
ISBN (Mycopy): 978-3-211-99357-6  
DOI 10.1007/978-3-211-99356-9  
Springer Wien Heidelberg New York Dordrecht London

Library of Congress Control Number: 2012952142

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